

## CORRECTION

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## Correction: Integration of $\text{BiFeO}_3/\text{La}_{0.7}\text{Sr}_{0.3}\text{MnO}_3$ heterostructures with III–V semiconductors for low-power non-volatile memory and multiferroic field effect transistors

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Correction for 'Integration of  $\text{BiFeO}_3/\text{La}_{0.7}\text{Sr}_{0.3}\text{MnO}_3$  heterostructures with III–V semiconductors for low-power non-volatile memory and multiferroic field effect transistors' by Md. Shafiqur Rahman *et al.*, *J. Mater. Chem. C*, 2016, **4**, 10386–10394.

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The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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